

	Hits	Search Text	DBs
22	15	((resist or photoresist or photosensitive or (radiation near5 sensitive)) same pattern\$4 same (etch\$4 or (dry near5 etch\$4) or RIE or ash\$4 or mill\$4) same (sidewall or side\$8 or top\$3portion or top\$4area or taper\$4 or vertical\$4 or slop\$3)) and develop\$4 and ((mill\$4 or ash\$4 or etch\$4 or RIE) same (gas\$4 or (inert\$4 near5 gas\$3) or plasma or ion\$3beam or ion\$4) same ((sulfur near2 oxide) or (sul\$3ur near2 \$2oxide) or ("SO.sub.2") or (sul\$2ur near9 containing)) same (He or Ne or Ar or Xe or Kr or "N.sub.2" or helium or neon or argon or "CO" or "CO.sub.2") same (oxygen or "O.sub.2") same (sccm or (flow near9 rate)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
23	22	((resist or photoresist or photosensitive or (radiation near5 sensitive)) same pattern\$4 same (etch\$4 or (dry near5 etch\$4) or RIE or ash\$4 or mill\$4) same (sidewall or side\$8 or top\$3portion or top\$4area or taper\$4 or vertical\$4 or slop\$3)) and ((mill\$4 or ash\$4 or etch\$4 or RIE) same (gas\$4 or (inert\$4 near5 gas\$3) or plasma or ion\$3beam or ion\$4) same ((sulfur near2 oxide) or (sul\$3ur near2 \$2oxide) or ("SO.sub.2") or (sul\$2ur near9 containing)) same (He or Ne or Ar or Xe or Kr or "N.sub.2" or nitrogen or helium or neon or argon or "CO" or "CO.sub.2" or (carbon near9 dioxide) or (carbon near9 \$4oxide)) same (oxygen or "O.sub.2") same (sccm or (flow near9 rate)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
24	16	((resist or photoresist or photosensitive or (radiation near5 sensitive)) same pattern\$4 same (etch\$4 or (dry near5 etch\$4) or RIE or ash\$4 or mill\$4) same (sidewall or side\$8 or top\$3portion or top\$4area or taper\$4 or vertical\$4 or slop\$3)) and ((mill\$4 or ash\$4 or etch\$4 or RIE) same (gas\$4 or (inert\$4 near5 gas\$3) or plasma or ion\$3beam or ion\$4) same ((sulfur near2 oxide) or (sul\$3ur near2 \$2oxide) or ("SO.sub.2") or (sul\$2ur near9 containing)) same (Ne or Ar or Xe or Kr or "N.sub.2" or nitrogen or neon or argon or "CO" or "CO.sub.2" or (carbon near9 dioxide) or (carbon near9 \$4oxide)) same (oxygen or "O.sub.2") same (sccm or (flow near9 rate)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
25	2	((resist or photoresist or photosensitive or (radiation near5 sensitive)) near16 (pattern\$4 or mask) near24 (strip\$4 or etch\$4 or (dry near5 etch\$4) or RIE or ash\$4 or mill\$4) near36 (residu\$4 or sidewall or side\$8 or top\$3portion or top\$4area or taper\$4 or vertical\$4 or slop\$3 or surface)) and ((strip\$4 or mill\$4 or ash\$4 or etch\$4 or RIE or (ion near9 beam)) near29 (gas\$4 or (inert\$4 near5 gas\$3) or plasma or ion\$3beam or ion\$4) near22 ((sulfur near2 oxide) or (sul\$3ur near2 \$2oxide) or ("SO.sub.2") or (sul\$2ur near9 containing)) near28 (Ne or Ar or Xe or Kr or "N.sub.2" or nitrogen or neon or argon or "CO" or "CO.sub.2" or (carbon near9 dioxide) or (carbon near9 \$4oxide)) near29 (oxygen or "O.sub.2") near33 (sccm or (flow near9 rate) or amount or \$2flux))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
26	1	((resist or photoresist or photosensitive or (radiation near5 sensitive)) near16 pattern\$4 near24 (strip\$4 or etch\$4 or (dry near5 etch\$4) or RIE or ash\$4 or mill\$4) near36 (residu\$4 or sidewall or side\$8 or top\$3portion or top\$4area or taper\$4 or vertical\$4 or slop\$3 or surface)) and ((strip\$4 or mill\$4 or ash\$4 or etch\$4 or RIE or (ion near9 beam)) near29 (gas\$4 or (inert\$4 near5 gas\$3) or plasma or ion\$3beam or ion\$4) near22 ((sulfur near2 oxide) or (sul\$3ur near2 \$2oxide) or ("SO.sub.2") or (sul\$2ur near9 containing)) near28 (Ne or Ar or Xe or Kr or "N.sub.2" or nitrogen or neon or argon or "CO" or "CO.sub.2" or (carbon near9 dioxide) or (carbon near9 \$4oxide)) near29 (oxygen or "O.sub.2") near33 (sccm or (flow near9 rate) or amount or \$2flux))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
27	26	((resist or photoresist or photosensitive or (radiation near5 sensitive)) near16 pattern\$4 near24 (strip\$4 or etch\$4 or (dry near5 etch\$4) or RIE or ash\$4 or mill\$4) near36 (residu\$4 or sidewall or side\$8 or top\$3portion or top\$4area or taper\$4 or vertical\$4 or slop\$3 or surface)) and ((strip\$4 or mill\$4 or ash\$4 or etch\$4 or RIE or (ion near9 beam)) near29 (gas\$4 or (inert\$4 near5 gas\$3) or plasma or ion\$3beam or ion\$4) near22 ((sulfur near2 oxide) or (sul\$3ur near2 \$2oxide) or ("SO.sub.2") or (sul\$2ur near9 containing)) near28 (Ne or Ar or Xe or Kr or "N.sub.2" or nitrogen or neon or argon or "CO" or "CO.sub.2" or (carbon near9 dioxide) or (carbon near9 \$4oxide)) near29 (oxygen or "O.sub.2"))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
28	4	((resist or photoresist or photosensitive or (radiation near5 sensitive)) near16 (mask or pattern\$4 or sidewall or T\$3top or (aspect near9 ratio)) near24 (strip\$4 or etch\$4 or (dry near5 etch\$4) or RIE or ash\$4 or mill\$4 or shrink\$5) near29 (gas\$4 or (inert\$4 near5 gas\$3) or plasma or ion\$3beam or ion\$4) near22 ((sulfur near2 oxide) or (sul\$3ur near2 \$2oxide) or ("SO.sub.2") or (sul\$2ur near9 containing)) near28 (Ne or Ar or Xe or Kr or "N.sub.2" or nitrogen or neon or argon or "CO" or "CO.sub.2" or (carbon near9 dioxide) or (carbon near9 \$4oxide)) near29 (oxygen or "O.sub.2"))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
29	5	((resist or photoresist or photosensitive or (radiation near5 sensitive)) near16 (mask or pattern\$4 or opening) near24 (strip\$4 or etch\$4 or (dry near5 etch\$4) or RIE or ash\$4 or mill\$4 or (ion near9 beam near4 etch\$4) or plasma) near29 ((sulfur near2 oxide) or (sul\$3ur near2 \$2oxide) or ("SO.sub.2") or (sul\$2ur near9 containing)) near28 (Ne or Ar or Xe or Kr or "N.sub.2" or nitrogen or neon or argon or "CO" or "CO.sub.2" or (carbon near9 dioxide) or (carbon near9 \$4oxide)) near29 (oxygen or "O.sub.2"))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
30	32	((resist or photoresist or photosensitive or (radiation near5 sensitive)) near16 (mask or pattern\$4 or opening) near24 (strip\$4 or etch\$4 or (dry near5 etch\$4) or RIE or ash\$4 or mill\$4 or (ion near9 beam near4 etch\$4) or plasma)) and ((shrink\$4 or reduc\$4 or remov\$4 or increase or etch\$4 or strip\$4) same (sidewall or surface or profile or via or trench) same (resist or photoresist) same (((sulfur near2 oxide) or (sul\$3ur near2 \$2oxide) or ("SO.sub.2") or (sul\$2ur near9 containing)) near28 (Ne or Ar or Xe or Kr or "N.sub.2" or nitrogen or neon or argon or xenon or krypton or "CO" or "CO.sub.2" or (carbon near9 dioxide) or (carbon near9 \$4oxide)) near29 (oxygen or "O.sub.2")) same plasma)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
31	81	((resist or photoresist or photosensitive or (radiation near5 sensitive)) near16 (mask or pattern\$4 or opening) near24 (strip\$4 or etch\$4 or (dry near5 etch\$4) or RIE or ash\$4 or mill\$4 or (ion near9 beam near4 etch\$4) or plasma)) and ((shrink\$4 or reduc\$4 or remov\$4 or etch\$4 or strip\$4) same (sidewall or surface or profile or via or trench or pattern or mask) same (resist or photoresist) same (((sulfur near2 oxide) or (sul\$3ur near2 \$2oxide) or ("SO.sub.2") or (sul\$2ur near9 containing)) near28 (Ne or Ar or Xe or Kr or "N.sub.2" or nitrogen or neon or argon or xenon or krypton or "CO" or "CO.sub.2" or (carbon near9 dioxide) or (carbon near9 \$4oxide)))) same plasma)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
32	49	S34 NOT S33	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
33	52	(((resist or photoresist or photosensitive or (radiation near5 sensitive)) near16 (mask or pattern\$4 or opening) near24 (strip\$4 or etch\$4 or (dry near5 etch\$4) or RIE or ash\$4 or mill\$4 or (ion near9 beam near4 etch\$4) or plasma)) same (shrink\$4 or reduc\$4 or remov\$4 or etch\$4 or strip\$4) same (sidewall or surface or profile or via or trench or pattern or mask or residu\$3) same (((sulfur near2 oxide) or (sul\$3ur near2 \$2oxide) or ("SO.sub.2") or (sul\$2ur near9 containing)) near28 (Ne or Ar or Xe or Kr or "N.sub.2" or nitrogen or neon or argon or xenon or krypton or "CO" or "CO.sub.2" or (carbon near9 dioxide) or (carbon near9 \$4oxide))))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
34	127	(((resist or photoresist or photosensitive or (radiation near5 sensitive)) near16 (strip\$4 or etch\$4 or (dry near5 etch\$4) or RIE or ash\$4 or mill\$4 or (ion near9 beam near4 etch\$4) or plasma)) same (shrink\$4 or reduc\$4 or remov\$4 or etch\$4 or strip\$4 or eliminat\$4) same (sidewall or surface or profile or via or trench or pattern or mask or residu\$3 or lateral\$3 or taper) same (((sulfur near2 oxide) or (sul\$3ur near2 \$2oxide) or ("SO.sub.2") or (sul\$2ur near9 containing)) near28 (Ne or Ar or Xe or Kr or "N.sub.2" or nitrogen or neon or argon or xenon or krypton or "CO" or "CO.sub.2" or (carbon near9 dioxide) or (carbon near9 \$4oxide))))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
35	52	(((resist or photoresist or photosensitive or (radiation near5 sensitive)) near16 (mask or pattern\$4 or opening) near24 (strip\$4 or etch\$4 or (dry near5 etch\$4) or RIE or ash\$4 or mill\$4 or (ion near9 beam near4 etch\$4) or plasma)) same (shrink\$4 or reduc\$4 or remov\$4 or etch\$4 or strip\$4) same (sidewall or surface or profile or via or trench or pattern or mask or residu\$3) same (((sulfur near2 oxide) or (sul\$3ur near2 \$2oxide) or ("SO.sub.2") or (sul\$2ur near9 containing)) near28 (Ne or Ar or Xe or Kr or "N.sub.2" or nitrogen or neon or argon or xenon or krypton or "CO" or "CO.sub.2" or (carbon near9 dioxide) or (carbon near9 \$4oxide))))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
36	75	S37 NOT S38	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
37	2	((resist or photoresist or photosensitive or (radiation near5 sensitive)) near16 (mask or pattern\$4) near24 (strip\$4 or etch\$4 or (dry near5 etch\$4) or RIE or ash\$4 or mill\$4) near29 (gas\$4 or (inert\$4 near5 gas\$3) or plasma or ion\$3beam or ion\$4) near22 ((sulfur near2 oxide) or (sul\$3ur near2 \$2oxide) or ("SO.sub.2") or (sul\$2ur near9 containing)) near28 (Ne or Ar or Xe or Kr or "N.sub.2" or nitrogen or neon or argon or "CO" or "CO.sub.2" or (carbon near9 dioxide) or (carbon near9 \$4oxide)) near29 (oxygen or "O.sub.2")) and ((plasma or etch\$4 or (ion near9 beam) or RIE) near22 (shrink\$4 or strip\$4 or linewidth or ash\$4) near29 (resist or photoresist) near36 (residu\$4 or pattern or mask))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB